● General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

● Features

■ Advance high cell density Trench technology

■Low $R_{DS(ON)}$ to minimize conductive loss

■Low Gate Charge for fast switching

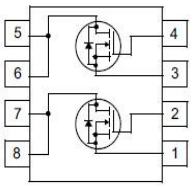
■Low Thermal resistance

●Application

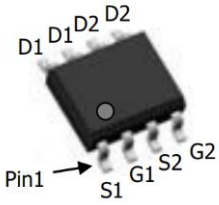
■SMPS 2nd Synchronous Rectifier

■BLDC Motor driver

● Product Summary



V_{DS1} =100V
V_{DS2} =100V
$R_{DS(ON)\ 1}$=10mΩ
$R_{DS(ON)\ 2}$=10mΩ
I_{D1} =12A
I_{D2} =12A



SOP8

RoHS

●Ordering Information:

Part NO.	ZMD68110S
Marking	ZMD68110
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

●Absolute Maximum Ratings (T_C =25℃)

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current②	$I_{D@}$TC=25℃	12	A
	$I_{D@}$TC=75℃	10.6	A
	$I_{D@}$TC=100℃	8.8	A
Pulsed Drain Current ①	I_{DM}	42	A
Total Power Dissipation②	P_D@TC=25℃	3.1	W
Total Power Dissipation	P_D@TA=25℃	0.69	W
Operating Junction Temperature	T_J	-55 to 150	℃
Storage Temperature	T_{STG}	-55 to 150	℃
Single Pulse Avalanche Energy	E_{AS}	150	mJ

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case②	R_{thJC}	-	-	40	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V,I_D =250uA	100			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	1.3		2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=100V, V_{GS} =0V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V ,V_{DS} =0V			±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A		10	12.8	mΩ
	$R_{DS(ON)}$	V_{GS}=10V, I_D=16A		12.5	15	mΩ
Forward Transconductance	g_{FS}	V_{DS} =25V, I_D=15A		15		s

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	Ciss	f = 1MHz	-	1400	-	pF
Output capacitance	Coss		-	630	-	
Reverse transfer capacitance	Crss		-	33	-	

Gate Charge characteristics(Ta= 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Qg	V_{DD} =30V	-	20	-	nC
Gate - Source charge	Qgs	I_D = 8A	-	3.6	-	
Gate - Drain charge	Qgd	V_{GS} = 10V	-	2.8	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

Fig.1 Gate-Charge Characteristics

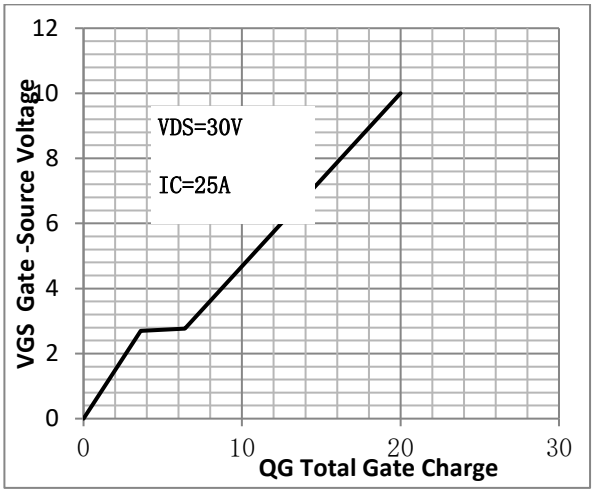


Fig.2 Capacitance Characteristics

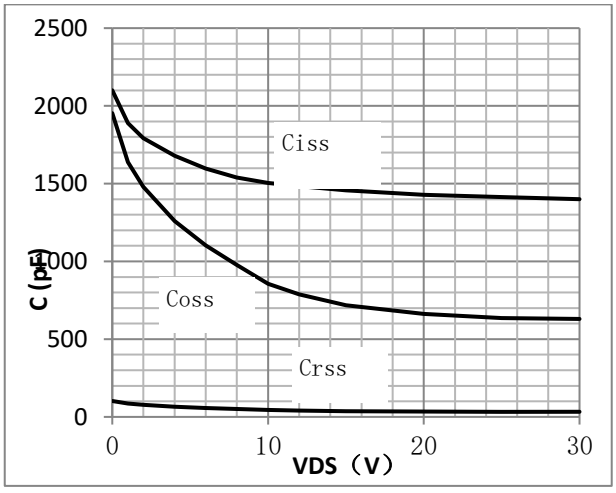


Fig.3 Power Dissipation

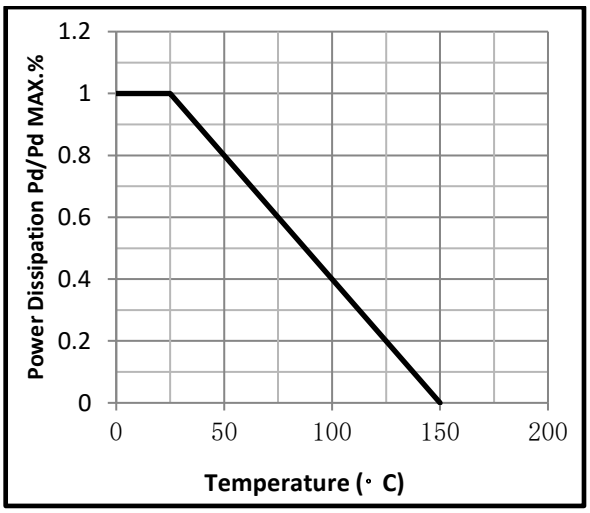


Fig.4 Typical output Characteristics

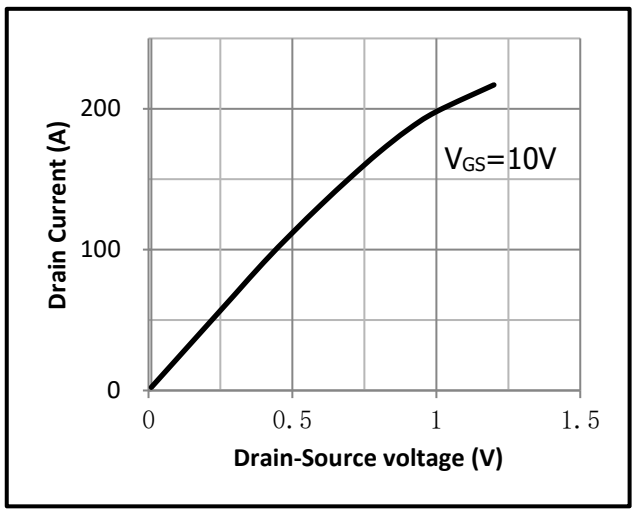


Fig.5 Threshold Voltage V.S Junction Temperature

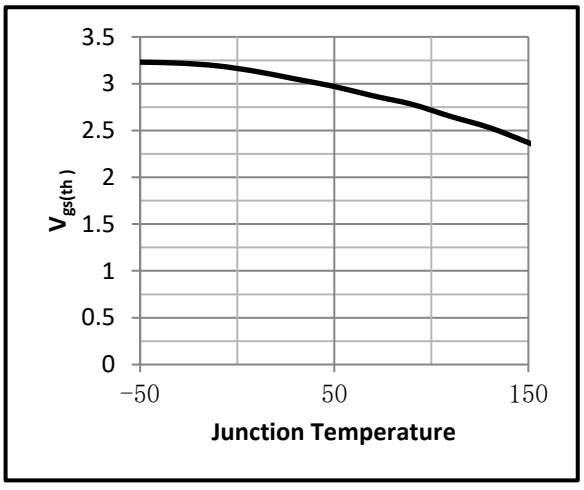


Fig.6 Resistance V.S Drain Current

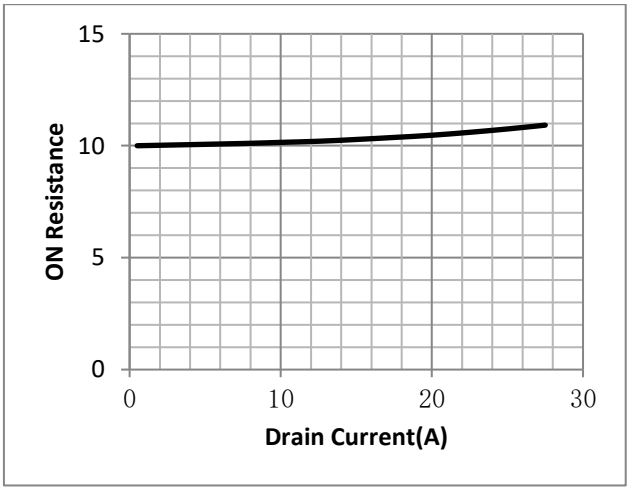


Fig.7 On-Resistance VS Gate Source Voltage

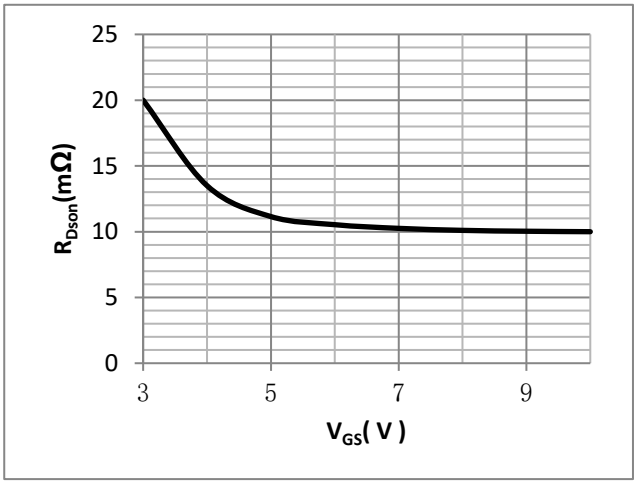


Fig.8 On-Resistance V.S Junction Temperature

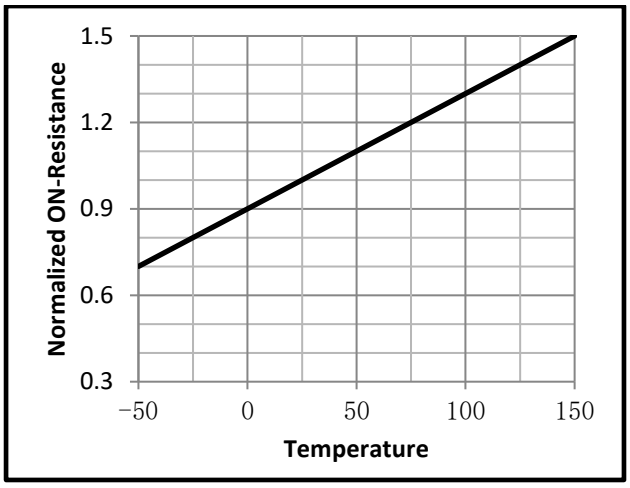


Fig.9 Switching Time Measurement Circuit

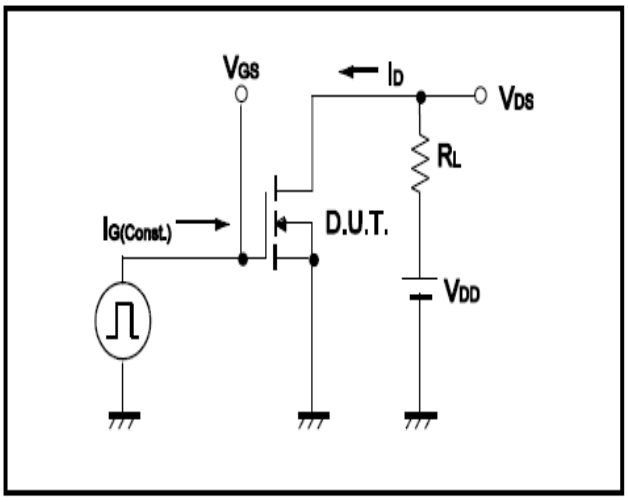


Fig.10 Gate Charge Waveform

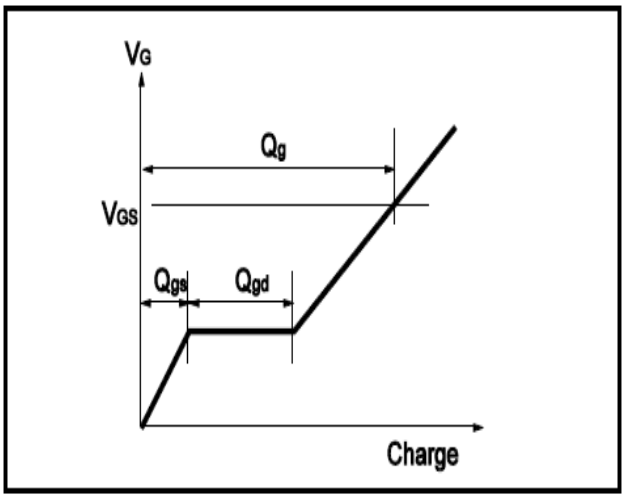


Fig.11 Switching Time Measurement Circuit

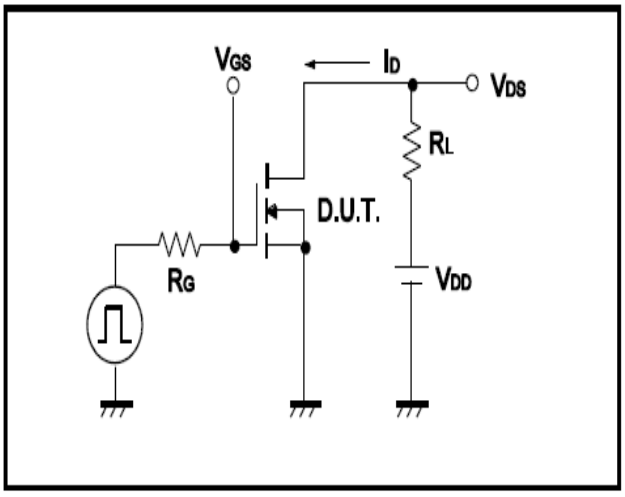
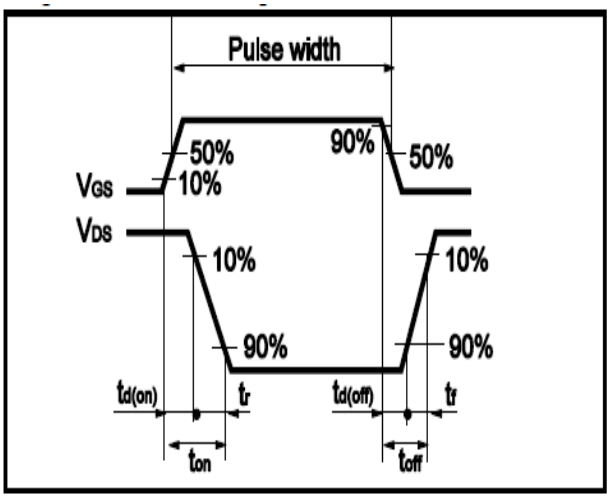


Fig.12 Gate Charge Waveform



•Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62